AUTOMOTIVE

RoHS

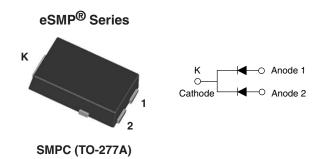
COMPLIANT

HALOGEN

FREE

Vishay Semiconductors

Hyperfast Rectifier, 2 x 3 A FRED Pt®



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LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS							
I _{F(AV)} 2 x 3 A							
V _R	200 V						
V _F at I _F	0.75 V						
t _{rr (typ.)}	27 ns						
T _J max.	175 °C						
Package	SMPC (TO-277A)						
Circuit configuration	Common cathode						

FEATURES

- Hyperfast recovery time, reduced Q_{rr} , and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMPC (TO-277A)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS compliant

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM R	ATINGS				
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage		V _{RRM}		200	V
Average restified forward current	per device	I _{F(AV)}	T _{Sp} = 165 °C	6	
Average rectified forward current	per diode			3	٨
Non-repetitive peak surge current	per device	1	$T = 25 ^{\circ}C$ 6 ma aquara pulaa	150	A
Non-repetitive peak surge current	per diode	IFSM	$T_J = 25 \ ^{\circ}C$, 6 ms square pulse	80	
Operating junction and storage ten	nperatures	T _J , T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	200	-	-	
Forward voltage, per diode	V _F	I _F = 3 A	-	0.87	0.94	V
		I _F = 3 A, T _J = 125 °C	-	0.75	0.79	
Reverse leakage current, per diode	1	$V_{R} = V_{R}$ rated	-	-	2	
neverse leakage current, per diode	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	2	10	μA
Junction capacitance	CT	V _R = 200 V	-	12	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		I _F = 1.0 A, dI _F /dt =	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$		27	-	
Reverse recovery time	+	I _F = 0.5 A, I _R = 1 A	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	25	
neverse recovery time	t _{rr}	T _J = 25 °C		-	20	-	A nC
		T _J = 125 °C		-	26	-	
Pool rocovery ourrent	I _{RRM}	T _J = 25 °C	I _F = 3 A dI _F /dt = 200 A/µs V _B = 160 V	-	2.4	-	
Peak recovery current		T _J = 125 °C		-	3.8	-	
	Q _{rr}	T _J = 25 °C		-	23	-	
Reverse recovery charge		T _J = 125 °C		-	50	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to mount, per diode	R _{thJM}		-	2.8	4	°C/W
Approximate weight				0.1		g
				0.0035		oz.
Marking device		Case style SMPC (TO-277A)		NC	H2	



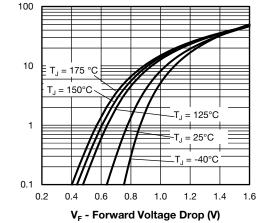


Fig. 1 - Typical Forward Voltage Drop Characteristics

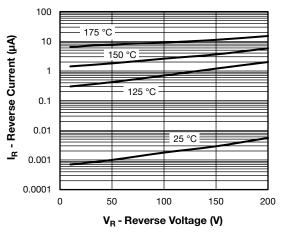
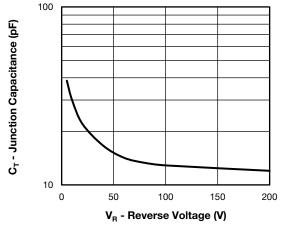


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

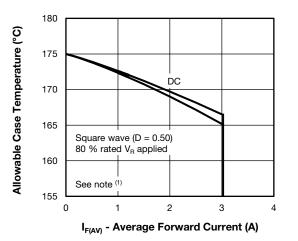


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

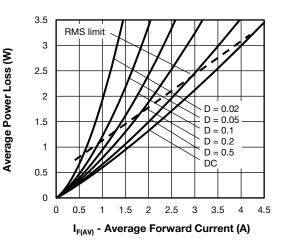


Fig. 5 - Forward Power Loss Characteristics

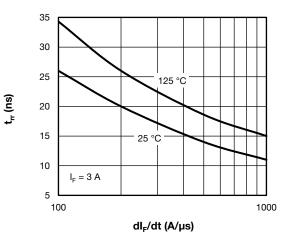


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt

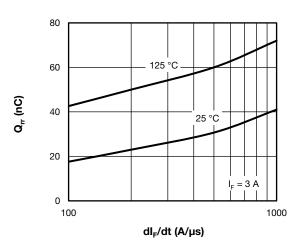


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (1 - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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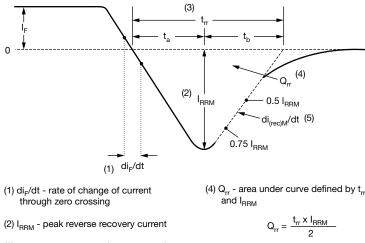
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(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

SHAY

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		1		1				
Device code	VS-	6	С	S	н	02	н	M3
		2	3	4	5	6	7	8
	1	- Visl	hay Sen	nicondu	ctors pro	oduct		
	2	- Cur	rent rati	ng (6 =	6 A)			
	3	- Circ	cuit conf	iguratio	า:			
		C =	commo	n catho	de			
	4	- S=	SMPC	package	9			
	5	- Pro	cess typ	be,				
		H =	hyper f	ast reco	very			
	6	- Vol	tage coo	de (02 =	200 V)			
	7	. н=	AEC-Q	101 qua	lified			
	8	- M3	= halog	en-free,	RoHS-0	complia	nt, and	termina

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-6CSH02HM3/86A	1500	1500	7" diameter plastic tape and reel			
VS-6CSH02HM3/87A	6500	6500	13" diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95570				
Part marking information	www.vishay.com/doc?95565				
Packaging information	www.vishay.com/doc?88869				
SPICE model	www.vishay.com/doc?96378				

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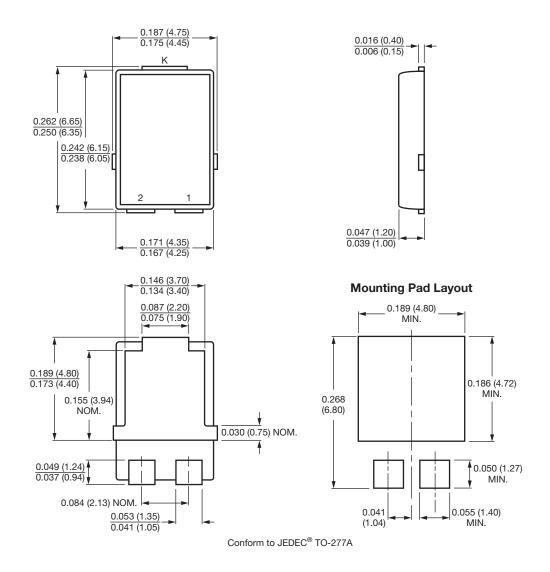
Outline Dimensions





TO-277A (SMPC)

DIMENSIONS in inches (millimeters)





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